



GaAs Wafer (Gallium Arsenide) Substrate MG Semiconductor materials

SUBSTRATE PROPERTY	MGGaAs2SIUPP-8000ME	MGGaAs3SIUPP-8000ME	MGGaAs4SIUPP-8000ME
Diameter	2 inch	3 inch	4 inch
Growth Method	VGF		
Conduction Type	Insulating		
Dopant	Undoped		
Crystal Orientation	(100)+/-0.5°		
Carrier Concentration	n/a		
Resistivity at RT	>1E7Ω·cm		
Mobility	>5000 cm²/V·sec		
Etch Pit Density	<8000cm⁻²		
Surface Finish	P/P		
Thickness	350~675 um		
Applications	Microelectronics		

*The other specifications can be customized according to customer's requirements